

PRE-ENCAPSULATED LEAD-FRAME CAVITY INTERPOSER

TECHNICAL FIELD

This invention relates generally to connectors for high density semiconductor
5 device configurations using a pre-encapsulated cavity interposer.

BACKGROUND

In response to the demand for semiconductor device packages having the
ability to include the largest number of semiconductor devices in the smallest
10 physical space, all components of such packages must occupy the least possible
physical volume and use the most efficient manner to interconnect with each other
and a power source.

It is known to form packages for semiconductor devices that include
semiconductor memory devices of different types as well as other semiconductor
15 devices with the package being connected to a printed circuit board. As it has
become desirable for the amount of physical space that the package occupies to
decrease, even though the number of semiconductor devices in the package is
increasing, and desirable to have improvements in attachment techniques used for
attaching the semiconductor devices to each other in the package itself and the
20 attachment of the package to a printed circuit board are necessary.

While the use of lead frames and wire bonds to connect semiconductor
devices is well known, such techniques can be further advanced. Similarly, while
the use of lead frames and flip-chip type attachment techniques to connect
semiconductor devices is well known, such techniques can be further advanced.
25 Additionally, while the use of solder bumps to connect semiconductor packages in
packages to printed circuit boards is well known, such can be further advanced.

DISCLOSURE OF THE INVENTION

A pre-encapsulated cavity interposer, a pre-encapsulated frame, for a
30 semiconductor device is disclosed.

DESCRIPTION OF THE DRAWINGS

FIG. 1 is a cross-sectional view of a pre-encapsulated frame;

FIG. 1A is a view of a portion of a strip of pre-encapsulated frames;

FIG. 1B is a view of a portion of a panel of pre-encapsulated frames;

5 FIG. 2 is a cross-sectional view of a pre-encapsulated frame having a semiconductor device installed therein;

FIG. 2A is a cross-sectional view of an alternative pre-encapsulated frame having a semiconductor device installed therein;

10 FIG. 2B is a cross-sectional view of an alternative pre-encapsulated frame having a semiconductor device installed therein;

FIG. 2C is a cross-sectional view of an alternative pre-encapsulated frame having a semiconductor device installed therein;

FIG. 2D is a cross-sectional view of an alternative pre-encapsulated frame having a semiconductor device installed therein;

15 FIG. 2E is a cross-sectional view of an alternative pre-encapsulated frame having a semiconductor device installed therein;

FIG. 3 is a cross-sectional view of two stacked pre-encapsulated frames each having a semiconductor device installed therein and connected using bond wires;

20 FIG. 4 is a cross-sectional view of a pre-encapsulated frame having a semiconductor device installed therein having two sides of bond pads on the active surface thereof;

FIG. 5 is a cross-sectional view of a pre-encapsulated frame having a semiconductor device installed therein having one side of bond pads on the active surface thereof;

25 FIG. 5A is a cross-sectional view of a pre-encapsulated frame having a semiconductor device installed therein having 1.5 sides of bond pads on the active surface thereof;

30 FIG. 5B is a cross-sectional view of a pre-encapsulated frame having a semiconductor device installed therein having one side of bond pads on the active surface thereof along the long side of the semiconductor device;

FIG. 5C is a plan view of a pre-encapsulated frame for a semiconductor device having two sides of bond pads on the active surface thereof;

FIG. 5D is a plan view of a pre-encapsulated frame for a semiconductor device having one side of bond pads on the active surface thereof;

FIG. 5E is a plan view of a pre-encapsulated frame for a semiconductor device having 1.5 sides of bond pads on the active surface thereof;

5 FIG. 5F is a plan view of a pre-encapsulated frame for a semiconductor device having one side of bond pads on the active surface thereof along the long side of the semiconductor device;

FIG. 6 is a cross-sectional view of two stacked pre-encapsulated frames having semiconductor devices installed therein being interconnected in a DDP
10 arrangement;

FIG. 7 is a cross-sectional view of four stacked pre-encapsulated frames having semiconductor devices installed therein being interconnected in a QDP arrangement;

FIG. 8 is a cross-sectional view of a pre-encapsulated frame having two
15 semiconductor devices installed therein in an offset arrangement;

FIG. 8A is a cross-sectional view of a pre-encapsulated frame having two semiconductor devices installed therein in a stacked arrangement;

FIG. 9 is a cross-sectional view of two stacked interconnected
pre-encapsulated frames, one frame having a DRAM semiconductor memory device
20 installed therein and the other frame having a NAND semiconductor memory device installed therein;

FIG. 10 is a cross-sectional view of three stacked interconnected
pre-encapsulated frames, one frame having a controller semiconductor device
installed therein and two frames having NAND semiconductor memory devices
25 installed therein;

FIG. 11 is a cross-sectional view of nine stacked interconnected
pre-encapsulated frames, one frame having a controller semiconductor device
installed therein and eight frames having NAND semiconductor memory devices
installed therein;

30 FIG. 12 is a cross-sectional view of two stacked interconnected pre-encapsulated frames, each frame having a semiconductor device having bond

pads on the active surface thereof arranged essentially in the center of the active surface essentially in a row;

FIG. 13 is a cross-sectional view of two stacked interconnected pre-encapsulated frames, each frame having a semiconductor device having bond pads on the active surface thereof arranged essentially in the center of the active surface essentially in two rows;

FIG. 14 is a cross-sectional view of five stacked interconnected pre-encapsulated frames located on a substrate, three frames having a NAND semiconductor devices installed therein, one frame having a DRAM semiconductor device installed therein, and one frame having a controller semiconductor device installed therein;

FIG. 15 is a cross-sectional view of a pre-encapsulated frame having an aperture therein;

FIG. 15A is a plan view of the pre-encapsulated frame of FIG. 15 from the bottom thereof;

FIG. 15B is a cross-sectional view of the pre-encapsulated frame of FIG. 15 having an imaging type semiconductor device installed therein and a lens installed therewith;

FIG. 15C is a cross-sectional view of a pre-encapsulated frame having an imaging type semiconductor device installed therein using bond wire type electrical connections and having a lens installed therewith;

FIG. 15D is a view of the process for installing an imaging type semiconductor device in the pre-encapsulated frame;

FIG. 16 is a cross-sectional view of six stacked interconnected pre-encapsulated frames, one frame having an imaging semiconductor device installed therein and a lens installed therewith, three frames having NAND semiconductor devices installed therein, one frame having a DRAM semiconductor device installed therein, and one frame having a controller semiconductor device installed therein;

FIG. 17 is a cross-sectional view of two stacked and interconnected pre-encapsulated frames, one frame having an imaging type semiconductor device

installed therein and a lens installed therewith and one frame having a lens installed therewith; and

FIG. 18 is a cross-sectional view of four pre-encapsulated frames, one frame having an imaging semiconductor device installed therein and a lens therewith and
5 three frames having lens installed therewith.

MODE(S) FOR CARRYING OUT THE INVENTION

Referring to drawing FIG. 1, a pre-encapsulated cavity interposer 10, hereinafter referred to as a pre-encapsulated interposer 10, is illustrated in
10 cross-section. The pre-encapsulated cavity interposer 10 comprises a pre-encapsulated member 11, the frame, formed of encapsulating compound 20 having any desired configuration for a semiconductor device to be retained in the member 11 in a cavity 22 therein and having a plurality of traces 12 including a first
15 portion 14, typically extending horizontally, having any desired shape and configuration, such as rectangular, square, etc. and a second portion 16, typically extending orthogonally from the first portion 14, although they may extend at any desired angle, as a post like structure having any desired shape and configuration, such as round, rectangular, square, hexagonal, triangular, elliptical, u-shaped, c-shaped, curved in cross-sectional shape, etc. As many second portions 16 of a
20 trace 12 may be attached in serial fashion to the first portion 14 of a trace 12 which are illustrated herein. The traces 12 include connection areas 18 formed in the ends of the second portions 16 which may include grooves therein or roughened surfaces thereon, as desired, for enhanced joint connections, although the connection areas 18 ends may be smooth, an encapsulating compound 20 covering portions of the
25 traces 12, and a cavity 22 formed by the traces 12 and encapsulation compound 20 of the frame member 11 for the installation of any desired number, shapes, and types of semiconductor devices therein. The cavity 22 surrounds and encloses any semiconductor device or semiconductor devices installed therein on the top and sides thereof. The cavity 22 having a desired size and a thickness essentially that
30 approximate the semiconductor device to be installed therein, although the cavity 22 can be any desired size and thickness for use with different types of semiconductor devices to be installed therein.

The traces 12 may be formed of any suitable metal material, such as copper, copper alloy, etc. of any desired thickness of metal material suitable for the application of the pre-encapsulated cavity interposer 10. Any desired metal coating, such as a layer of gold, silver, nickel, palladium, alloys thereof, etc. and/or any
5 desired coating of material may be used on the traces 12 at any desired location thereon for any purpose. The encapsulating material or compound 20 may be of any suitable type for the application for the pre-encapsulated cavity interposer 10 and may contain any suitable amount of filler material and other additives therein, if desired for the formation of the pre-encapsulated frame 11. The encapsulation
10 material 20 surrounds each trace 12 insulating the trace 12 while providing a suitable connection area 15 on the first portion 14 for connection to a semiconductor device and connection areas 18 on the second portion. The connection area 15 may include any desired layers of metal thereon, such as gold, silver, nickel, palladium, alloys thereof, etc. The surface 24 formed opposite of the cavity 22 of the
15 pre-encapsulated cavity interposer 10 is generally planar having areas free of encapsulation material for the connection areas 18 of the second portions 16 of the traces 12. If desired, the surface 24 may include other areas free of encapsulation material 20 for connection areas for the first portion 14 of a trace 12 (not shown) so that both the first portion 14 and second portion 16 of a trace may include
20 connection areas on the upper and lower surfaces thereof. Similarly, if desired, the surface 24 may have a cavity of any desired sized and shape, such as cavity 22, formed therein (not shown).

The pre-encapsulated cavity interposer 10 may be formed in strip form of any desired length and configuration pattern or in panel form having any desired
25 geometric shape and physical size. The pre-encapsulated cavity interposer 10 is constructed using a base material (not shown), having the traces 12 patterned on the base material having any size, pitch, pattern, shape, thickness, length, etc. with the encapsulation material 20 providing support for the traces 12 being applied thereover. After the formation of the pre-encapsulated cavity interposer 10 on the
30 base material, the base material is removed leaving the pre-encapsulation interposer 10. The pre-encapsulated cavity interposer 10 may be formed for stacking of multiple pre-encapsulation frames having any desired number of

semiconductor devices therein one on top the other being electrically interconnected by the connection areas 18 of the ends of the second portions 16 of the traces 12 contacting each other as desired.

Referring to drawing FIG. 1A, illustrated in a top view is a portion of a strip
5 of pre-encapsulation interposers 10 which may be cut or severed into individual pre-encapsulation interposers 10 at any desired time of use.

Referring to drawing FIG. 1B, illustrated in a top view is a portion of a panel of pre-encapsulation interposers 10 which may be cut or severed into individual pre-encapsulation interposers 10 at any desired time of use.

10 Referring to drawing FIG. 2, the pre-encapsulated cavity interposer 10 is illustrated in cross-section having a flip-chip type semiconductor device 30 attached to connection areas 15 of the first portions 14 of traces 12 using solder balls 32, or solder bumps, solder stud bumps, or gold stud bumps located between bond pads of the semiconductor device 30 and the connection areas 15. The cavity 22 of the
15 pre-encapsulated cavity interposer 10 having the semiconductor device 30 located therein is filled with any suitable liquid encapsulant material, underfill material, etc. to retain and environmentally seal the semiconductor device 30 in the cavity 22 forming an essentially planar lower surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the
20 lower surface 18 of the second portion 16 of traces 12.

Referring to drawing FIG. 2A, the pre-encapsulated cavity interposer 10 is illustrated in cross-section having a flip-chip type semiconductor device 30 attached to connection areas 15 which extend below the lower surface 20' of the encapsulant material 20 covering the lower surface 18 of the second portion 16 of the traces 12
25 having one or more grooves or recesses 15' therein of the first portions 14 of a leads 12 using solder balls 32, or solder bumps, solder stud bumps, or gold stud bumps located between bond pads of the semiconductor device 30 and the connection areas 15. The one or more grooves or cavities 15' in the connection areas facilitate the location of the semiconductor device 30 in the cavity 22 in the
30 proper location with respect to connection areas 15 using conventional semiconductor device attachment equipment. The one or more grooves or cavities 15' may be formed having any suitable geometric shape and desired depth in

the connections areas 15 by any suitable method, such as etching, coining, laser forming, etc. The cavity 22 of the pre-encapsulated cavity interposer 10 having the semiconductor device 30 located therein is filled with any suitable liquid encapsulant material, underfill material, etc. to retain and environmentally seal the semiconductor device 20 in the cavity 22 forming an essentially planar lower surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the lower surface 18 of the second portion 16 of traces 12.

Referring to drawing FIG. 2B, the pre-encapsulated cavity interposer 10 is illustrated in cross-section having a flip-chip type semiconductor device 30 attached to connection areas 15 which extend below the lower surface 20' of the encapsulant material 20 covering the lower surface 18 of the second portion 16 of the traces 12 having two or more grooves or recesses 15' therein of the first portions 14 of a leads 12 using two or more solder balls 32, or solder bumps, solder stud bumps, or gold stud bumps located between bond pads of the semiconductor device 30 and the connection areas 15. The two or more grooves or cavities 15' in the connection areas facilitate the location of the semiconductor device 30 in the cavity 22 in the proper location with respect to connection areas 15 using conventional semiconductor device attachment equipment. The two or more grooves or cavities 15' may be formed having any suitable geometric shape and desired depth in the connections areas 15 by any suitable method, such as etching, coining, laser forming, etc. The cavity 22 of the pre-encapsulated cavity interposer 10 having the semiconductor device 30 located therein is filled with any suitable liquid encapsulant material, underfill material, etc. to retain and environmentally seal the semiconductor device 20 in the cavity 22 forming an essentially planar lower surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the lower surface 18 of the second portion 16 of traces 12.

Referring to drawing FIG. 2C, the pre-encapsulated cavity interposer 10 is illustrated in cross-section having a flip-chip type semiconductor device 30 attached to connection areas 15 which are located at essentially the same level as the lower surface 20' of the encapsulant 20 having one or more grooves or recesses 15' therein

of the first portions 14 of a leads 12 using solder balls 32, or solder bumps, solder stud bumps, or gold stud bumps located between bond pads of the semiconductor device 30 and the connection areas 15. The one or more grooves or cavities 15' in the connection areas facilitate the location of the semiconductor device 30 in the cavity 22 in the proper location with respect to connection areas 15 using conventional semiconductor device attachment equipment. The one or more grooves or cavities 15' may be formed having any suitable geometric shape and desired depth in the connections areas 15 by any suitable method, such as etching, coining, laser forming, etc. The cavity 22 of the pre-encapsulated cavity interposer 10 having the semiconductor device 30 located therein is filled with any suitable liquid encapsulant material, underfill material, etc. to retain and environmentally seal the semiconductor device 20 in the cavity 22 forming an essentially planar lower surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the lower surface 18 of the second portion 16 of traces 12.

Referring to drawing FIG. 2D, the pre-encapsulated cavity interposer 10 is illustrated in cross-section having a flip-chip type semiconductor device 30 attached to connection areas 15 which extend below the lower surface 20' of the encapsulant material 20 covering the lower surface 18 of the second portion 16 of the traces 12 having two or more grooves or recesses 15' therein of the first portions 14 of a leads 12 using two or more solder balls 32, or solder bumps, solder stud bumps, or gold stud bumps located between bond pads of the semiconductor device 30 and the connection areas 15. The two or more grooves or cavities 15' in the connection areas facilitate the location of the semiconductor device 30 in the cavity 22 in the proper location with respect to connection areas 15 using conventional semiconductor device attachment equipment. The two or more grooves or cavities 15' may be formed having any suitable geometric shape and desired depth in the connections areas 15 by any suitable method, such as etching, coining, laser forming, etc. The cavity 22 of the pre-encapsulated cavity interposer 10 having the semiconductor device 30 located therein is filled with any suitable liquid encapsulant material, underfill material, etc. to retain and environmentally seal the semiconductor device 20 in the cavity 22 forming an essentially planar lower

surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the lower surface 18 of the second portion 16 of traces 12.

Referring to drawing FIG. 2E, the pre-encapsulated cavity interposer 10 is illustrated in cross-section having a flip-chip type semiconductor device 30 attached to connection areas 15 which are located at essentially the same level as the lower surface 20' of the encapsulant 20 having a roughened surface 15' therein of the first portions 14 of a leads 12 using solder balls 32, or solder bumps, solder stud bumps, or gold stud bumps located between bond pads of the semiconductor device 30 and the connection areas 15. The roughened surface 15' in the connection areas 15 facilitate the location of the semiconductor device 30 in the cavity 22 in the proper location with respect to connection areas 15 using conventional semiconductor device attachment equipment. The roughened surface 15' may be formed having any suitable geometric shape and desired depth in the connections areas 15 by any suitable method, such as etching, coining, laser forming, etc. The cavity 22 of the pre-encapsulated cavity interposer 10 having the semiconductor device 30 located therein is filled with any suitable liquid encapsulant material, underfill material, etc. to retain and environmentally seal the semiconductor device 20 in the cavity 22 forming an essentially planar lower surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the lower surface 18 of the second portion 16 of traces 12.

Referring to drawing FIG. 3, a pair of pre-encapsulated cavity interposers 10 are illustrated in cross-section, each having a semiconductor device 30 located in cavity 22. Each semiconductor device 30 is attached to the encapsulation material 20 using a suitable adhesive 38, which may be either a layer of adhesive or a double-sided adhesive tape, to retain the semiconductor device 20 in the cavity 22 prior to the filling of the cavity 22 with any suitable liquid encapsulant material, underfill material, etc. to retain and environmentally seal the semiconductor device 20 in the cavity 22 forming an essentially planar lower surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the lower surface 36 of the second portion 16 of traces 12. As illustrated, the first portions of the traces 12 are connected to the bond pads of the

semiconductor device 30 using bond wires 40, rather than a flip-chip style type of attachment. If desired, an anisotropic conductive film 42 (shown in dashed lines) or non conductive film 42 (shown in dashed lines) may be used to seal the semiconductor device in the cavity 22 without the use of the encapsulant material 34 in the cavity 22. A solder paste 44 may be applied to the connection areas 18 of the second portion of traces 12 for reflow and connection of the pre-encapsulated cavity interposers 10.

Referring to drawing FIG. 4, the pre-encapsulation interposer 10 is illustrated in cross-section having a flip-chip type semiconductor device 30 having bond pads on the active surface thereof about two sides of the semiconductor device 30 attached to the first portion 14 of the traces 12 with the cavity 22 filled with any suitable liquid encapsulant material, underfill material, etc. to retain and seal the semiconductor device 20 in the cavity 22 forming an essentially planar lower surface 36 opposite the surface 24 of the pre-encapsulated cavity interposer 10 at essentially the same level as that of the lower surface 36 of the second portion 16 of traces 12. If desired, a layer of adhesive or a double-sided adhesive tape 38 may be used to retain the semiconductor device 30 in the cavity 22 prior to the reflow of the solder balls 32 to attach the semiconductor device 30 to the connection areas 15 of the first portion 14 of the traces 12.

Referring to drawing FIG. 5, the pre-encapsulated cavity interposer 10 is illustrated in cross-section configured to a semiconductor device 30 having bond pads on the active surface thereof along one side thereof. The traces 12 are formed in a pattern so that a first portion 14 of one trace is longer than the first portion 14 of another trace 12 to connect to a desired bond pad on the semiconductor device 30 in a flip-chip style type of arrangement described hereinbefore.

Referring to drawing FIG. 5A, the pre-encapsulated cavity interposer 10 is illustrated in cross-section configured to a semiconductor device 30 having bond pads on the active surface thereof in a 1.5-sided configuration as known in the art. The traces 12 are formed in a pattern so that a first portion 14 of one trace is longer than the first portion 14 of another trace 12 to connect to a desired bond pad on the semiconductor device 30 in a flip-chip style type of arrangement described hereinbefore.

Referring to drawing FIG. 5B, the pre-encapsulated cavity interposer 10 is illustrated in cross-section configured to a semiconductor device 30 having bond pads on the active surface thereof solely along the long side of the semiconductor device 20. The traces 12 are formed to in a pattern to vary in length and configuration so that the first portion 14 of a trace connects to a desired bond pad of the semiconductor device 30 in a flip-chip style type arrangement described hereinbefore.

Referring to drawing FIG. 5C, a pre-encapsulated cavity interposer 10 is illustrated in a plan view to show the layout of the traces 12 for a two-sided bond pad configuration for a semiconductor device 30 having bond pads on the active surface thereof located on two sides of the semiconductor device 30. As illustrated the second portions 16 of the traces 12 extend from each side of the pre-encapsulated cavity interposer 10 to extend over the bond pads 31 located on the semiconductor die 30. The pre-encapsulated interposer 10 is typically used for a semiconductor device 30 such as described in drawing FIG. 4.

Referring to drawing FIG. 5D, a pre-encapsulated cavity interposer 10 is illustrated in plan view to show the layout of the traces 12 for a one-sided bond pad configuration for a semiconductor device 30 having bond pads on the active surface thereof located on one side of the semiconductor device 30. As illustrated the second portions 16 of the traces 12 extend from each side of the pre-encapsulated cavity interposer 10 to extend over the bond pads 31 located on the semiconductor die 30. The pre-encapsulated cavity interposer 10 is typically used for a semiconductor device 30 such as described in drawing FIG. 5.

Referring to drawing FIG. 5E, a pre-encapsulated cavity interposer 10 is illustrated in plan view to show the layout of the traces 12 for a 1.5-sided bond pad configuration for a semiconductor device 30 having bond pads on the active surface thereof located on 1.5 sides of the semiconductor device 30. As illustrated the second portions 16 of the traces 12 extend from each side of the pre-encapsulated interposer 10 to extend over the bond pads 31 located on the semiconductor die 30. The pre-encapsulated interposer 10 is typically used for a semiconductor device 30 such as described in drawing FIG. 5A.

Referring to drawing FIG. 5F, a pre-encapsulated interposer 10 is illustrated in plan view to show the layout of the traces 12 for a one-sided bond pad configuration for a semiconductor device 30 having bond pads on the active surface thereof located on a long side of the semiconductor device 30. As illustrated the second portions 16 of the traces 12 extend from each side of the pre-encapsulated cavity interposer 12 to extend over the bond pads 31 located on the semiconductor die 30. The pre-encapsulated interposer 10 is typically used for a semiconductor device 30 such as described in drawing FIG. 5B.

Referring to drawing FIG. 6, the pre-encapsulation interposer 10 is illustrated in cross-section where two pre-encapsulation interposers 10 are stacked and connected in DDP form by reflowed solder paste 44 connecting the connecting surfaces 18 of the second portions 16 of the traces 12. The semiconductor devices 30 are attached to the first portions 14 of the traces 12 in a flip-chip style type of arrangement described hereinbefore.

Referring to drawing FIG. 7, the pre-encapsulation interposer 10 is illustrated in cross-section where four pre-encapsulation interposers 10 are stacked and connected in QDP form by reflowed solder paste 44 connecting the connecting surfaces 18 of the second portions 16 of the traces 12. The semiconductor devices 30 are attached to the first portions 14 of the traces 12 in a flip-chip style type of arrangement described hereinbefore.

Referring to drawing FIG. 8, the pre-encapsulation interposer 10 is illustrated in cross-section configured to connect to two semiconductor devices 30 having bond pads on the active surface thereof in a one-sided configuration as known in the art. The traces 12 are formed in a pattern so that a first portion 14 of one trace is longer than the first portion 14 of another trace 12 to connect to a desired bond pad on the semiconductor device 30 in a flip-chip style type of arrangement described hereinbefore. An adhesive 38 may attach the semiconductor device 30 to the encapsulated traces 12 and to each other. The semiconductor devices 30 are stacked having an offset from each other along the side of the semiconductor device 30 having the bond pads located there along. As illustrated, some of the traces 12 are formed having a stepped second portion 14' to attach to bond pads on one side of the lower semiconductor device 30.

Referring to drawing FIG. 8A, the pre-encapsulation interposer 10 is illustrated in cross-section configured to connect to two semiconductor devices, a controller semiconductor device 60 and a NAND semiconductor device 50, each having bond pads on the active surface thereof as described herein as known in the art. The traces 12 are formed in a pattern so that an upper first portion 14 of one trace connects to bond pads of the controller semiconductor device 60 while the lower first portions 14' connect to bond pads on the active surface of a NAND semiconductor device 50 in flip-chip style types of arrangement described hereinbefore. An insulating adhesive or suitable insulating adhesive tape 38' may attach the semiconductor device 60 to the encapsulated traces 12 and to the semiconductor device 50. The semiconductor devices 30 are in a stacked arrangement with the pre-encapsulation interposer 10 being thicker to accommodate two semiconductor devices therein with the cavity 22 being a stepped arrangement to accommodate two semiconductor devices having different sizes. The cavity 22 is filled and environmentally sealed with a suitable encapsulant 36.

Referring to drawing FIG. 9, the pre-encapsulation interposer 10 is illustrated in cross-section in a stacked and interconnected configuration for use with a semiconductor device 60, such as a controller semiconductor device known in the art, and another semiconductor device 50, such as a DRAM or NAND flash memory type semiconductor device, in a stacked configuration. Both of the pre-encapsulation interposers 10 have been formed having two second portions 16 for the traces 12. The upper pre-encapsulation interposer 10 is formed having the first portions 14 of the traces 12 configured to attach to the bond pads of the semiconductor device 60 which are located solely along one side thereof, such as described in drawing FIG. 5B hereinbefore in a flip-chip style type arrangement. The lower pre-encapsulation interposer 10 is formed with the first portions 14 of the traces 12 configured for attachment to the bond pads on the active surface of the semiconductor device 50 which are located along two sides thereof in a flip-chip style type arrangement as described herein.

Referring to drawing FIG. 10, the pre-encapsulation interposer 10 is illustrated in cross-section in a stacked and interconnected configuration for use with a semiconductor device 60, such as a controller semiconductor device known in the

art, and two semiconductor devices 30, such as a NAND flash memory type semiconductor device. All of the pre-encapsulation interposers 10 have been formed having two second portions 16 for the traces 12. The upper pre-encapsulation interposer 10 is formed having the first portions 14 of the traces 12 configured to
5 attach to the bond pads of the semiconductor device 30 which are located solely along one side thereof, such as described in drawing FIG. 5B hereinbefore in a flip-chip style type arrangement. The lower pre-encapsulation interposers 10 are formed with the first portions 14 of the traces 12 configured for attachment to the bond pads on the active surface of the semiconductor device 50 which are located
10 along two sides thereof in a flip-chip style type arrangement as described herein.

Referring to drawing FIG. 11, the pre-encapsulation interposer 10 is illustrated in cross-section in a stacked and interconnected configuration for use with semiconductor device 60, such as a controller semiconductor device known in the art, and eight other semiconductor devices 50, such as a NAND flash memory type
15 semiconductor device, in a stacked configuration. All pre-encapsulation interposers 10 have been formed having two second portions 16 for the traces 12. The upper pre-encapsulation interposer 10 is formed having the first portions 14 of the traces 12 configured to attach to the bond pads of the semiconductor device 60 which are located solely along one side thereof, such as described in drawing
20 FIG. 5B hereinbefore in a flip-chip style type arrangement. The lower pre-encapsulation interposer 10 is formed with the first portions 14 of the traces 12 configured for attachment to the bond pads on the active surface of the semiconductor device 50 which are located along two sides thereof in a flip-chip style type arrangement as described herein.

25 Referring to drawing FIG. 12, the pre-encapsulation interposer 10 is illustrated in cross-section in a stacked and interconnected configuration for use with semiconductor devices 50, such as DRAM flash memory type semiconductor device having the bond pads located on the active surface thereof in essentially a single column in essentially the center of the active surface. Both pre-encapsulation
30 interposers 10 have been formed having two second portions 16 for the traces 12. The upper pre-encapsulation interposer 10 is formed having the first portions 14 of the traces 12 configured to attach to the bond pads of the semiconductor device 50

hereinbefore in a flip-chip style type arrangement. Each pre-encapsulation interposer 10 is connected to the other by reflowed solder paste 44 between the connection areas 18 of the second portions 16 of the traces 12.

Referring to drawing FIG. 13, the pre-encapsulation interposer 10 is illustrated in cross-section in a stacked and interconnected configuration for use with semiconductor devices 50, such as DRAM flash memory type semiconductor device, having the bond pads located on the active surface thereof in essentially a two columns in essentially the center portion of the active surface of the semiconductor devices 50. Both pre-encapsulation interposers 10 have been formed having two second portions 16 for the traces 12. The upper pre-encapsulation interposer 10 is formed having the first portions 14 of the traces 12 configured to attach to the bond pads of the semiconductor device 50 hereinbefore in a flip-chip style type arrangement. Each pre-encapsulation interposer 10 is connected to the other by reflowed solder paste 44 between the connection areas 18 of the second portions 16 of the traces 12.

Referring to drawing FIG. 14, the pre-encapsulation interposer 10 is illustrated in cross-section in a stacked and interconnected configuration for with use for a variety of different types of semiconductor devices 50, 60 having bond pads located on their active surfaces along a number of sides thereof as described hereinbefore with all semiconductor devices 50, 60 connected to circuits on a suitable substrate 1, such as a printed circuit board. All pre-encapsulation interposers 10 have been formed having three second portions 16 for the traces 12. The upper pre-encapsulation interposer 10 is formed having the first portions 14 of the traces 12 configured to attach to the bond pads of the semiconductor device 50 hereinbefore in a flip-chip style type arrangement. Each pre-encapsulation interposer 10 is connected to the other and to the circuits on the substrate 1 by reflowed solder paste 44 between the connection areas 18 of the second portions 16 of the traces 12 and the circuits on the substrate 1.

Referring to drawing FIG. 15, a pre-encapsulation interposer 10 is illustrated in cross-section in a configuration for use with a CMOS imager semiconductor device (not illustrated). The pre-encapsulation interposer 10 includes a central aperture 11 therein.

Referring to drawing FIG. 15A, the pre-encapsulation interposer 10 illustrated in cross-section in FIG. 15 is illustrated in a top view showing the four sides forming the pre-encapsulation interposer 10, the central aperture 11, first portion 14 and second portion 16 of traces 12, and encapsulation material 20.

5 Referring to drawing FIG. 15B, the pre-encapsulation interposer 10 is illustrated in cross-section having a CMOS imager semiconductor device 70 having an imaging area 72 connected in a flip-chip style to using gold to solder bumps to the first portion 14 of the traces 12 and having a glass 74, a transparent member, located over central aperture 11 contacting the upper surface 24 of the
10 encapsulant 20 and attached to the CMOS imager semiconductor device 70 by members 76 extending from the lower surface 78 of the glass 74, through the aperture 11, and attached to the CMOS imager semiconductor device 70.

Referring to drawing FIG. 15C, the pre-encapsulation interposer 10 is illustrated in cross-section having a CMOS imager semiconductor device 70
15 attached to encapsulant 20 using a suitable adhesive with the CMOS imager semiconductor device 70 connected to first portions 14 of the traces 12 using bond wires. The glass 74 is located over aperture 11 having the members 76 attaching the glass to the encapsulant 20. The second portions 16 of traces 12 are formed having connection areas 18.

20 Referring to drawing FIG. 15D, the pre-encapsulation interposer 10 is illustrated in cross-section, as in drawing FIG. 15 and top view in drawing FIG. 15A, for the first step in the forming of the CMOS imager semiconductor device 70 attachment thereto in a flip-chip style. In step 2, the CMOS imager semiconductor device 70 is attached to the first portions 14 of the traces 12 using
25 gold to reflowed solder ball or bump type attachment in a flip-chip type style. In step 3, the members 76 are attached to the CMOS imager semiconductor device 70 using a suitable type adhesive. In step 4, the glass 74 is attached to the members 74 using a suitable adhesive. In step 5, a suitable encapsulant 34 is used to fill the cavity 22 to seal the CMOS imager semiconductor device 70 in the
30 pre-encapsulation interposer 10. In step 6, solder paste 44 is applied to contact areas 18 of the second portion 16 of the traces 12 for connection of the CMOS imager semiconductor device 70 to a camera chip module (not shown). This process

may also be used for a CMOS imager semiconductor device 70 having connections to the first portions 14 of the traces 12 using bond wires as described herein with respect to drawing FIG. 15C.

Referring to drawing FIG. 16, the pre-encapsulation interposer 10 is
5 illustrated in cross-section as shown in drawing FIG. 15C having a CMOS imager semiconductor device 70 attached thereto and a series of pre-encapsulation interposers 10 having various semiconductor devices attached thereto in a stacked configuration as illustrated in drawing FIG. 14.

Referring to drawing FIG. 17, the pre-encapsulation interposer 10 is
10 illustrated in cross-section as shown in drawing FIG. 15C having a CMOS imager semiconductor device 70 attached thereto and an additional pre-encapsulation interposer 10 having a additional lens 86 attached to first portions 14 of traces 12 by a suitable adhesive 88 in cavity 22 of the pre-encapsulation interposer 10. The second portions 16 of the traces 12 are connected using solder paste 44 at the
15 connection areas 18 of the second portions 16. As many additional lenses 86 may be attached to pre-encapsulation interposers 10 and stacked on a preceding pre-encapsulation interposer 10 having a lens 86 installed therein.

Referring to drawing FIG. 18, a pre-encapsulation interposer 10 is illustrated in cross-section as shown in drawing FIG. 15C having a CMOS imager 70 attached
20 thereto and an additional pre-encapsulation interposers 10 having an additional lens 86 attached to first portions 14 of traces 12 by a suitable adhesive 88 in cavity 22 of the pre-encapsulation interposer 10. The second portions 16 of the traces 12 are connected using solder paste 44 at the connection areas 18 of the second portions 16. As many additional lenses 86 may be attached to
25 pre-encapsulation interposers 10 and stacked on a preceding pre-encapsulation interposer 10 having a lens 86 installed therein. As illustrated, the additional two lenses 86 are used for an optical zoom effect for a camera module (not shown).

Having described the inventions of the pre-encapsulated interposer frame, it will be apparent to one of ordinary skill in the art that changes and modifications
30 may be made thereto, such as the addition of vertical molded guides in the cavity of the pre-encapsulated interposer frame to guide a semiconductor device in position in the cavity, using a pre-encapsulated interposer frame to house three or more

semiconductor devices, the use of four or more second portions of the traces connected to first portions of the traces to connect to a semiconductor device, etc. Such changes or modifications are intended to be covered by the claimed inventions.

CLAIMS

What is claimed is:

- 5 1. A semiconductor assembly including a pre-encapsulated frame, the assembly comprising:
a structure comprising an encapsulation material and having a cavity therein, the cavity having a portion of the structure extending thereover and another portion extending therearound;
10 at least two semiconductor devices located in the cavity of the structure in a flip-chip configuration; and
a plurality of traces located in the encapsulation material of the structure, each trace having an upper first portion connected to a first semiconductor device of the at least two semiconductor devices extending in the portion of the structure
15 extending over the cavity, a lower first portion connected to a second semiconductor device of the at least two semiconductor devices extending in the portion of the structure extending over the cavity, and a second portion extending in the another portion of the structure connected to the first portion, one end of the second portion being exposed for connection thereto,
20 wherein the upper first portion of at least one trace of the plurality of traces has a length greater than a length of the lower first portion of the at least one trace of the plurality of traces.
- 25 2. The assembly of claim 1, wherein the one end of the second portion of a trace of the plurality of traces includes at least one of one or more recesses therein and a roughened surface.
- 30 3. The assembly of claim 1, wherein the plurality of traces comprises:
a first plurality of traces having a first portion extending from one side of the structure across a portion of the cavity; and
a second plurality of traces having a first portion extending from another side of the structure across a portion of the cavity.

4. The assembly of claim 3, wherein the plurality of traces further comprises:
a third plurality of traces having a first portion extending from a third side of the
5 structure across a portion of the cavity.

5. The assembly of claim 4, wherein the plurality of traces further comprises:
a fourth plurality of traces having a first portion extending from a fourth side of the
10 structure across a portion of the cavity.

6. The assembly of claim 1, wherein the second portion of a trace includes two portions exposed from the structure.

15 7. The assembly of claim 1, wherein another end of a trace is exposed for connection thereto.

8. The assembly of claim 1, wherein the pre-encapsulated frame comprises one of a strip of pre-encapsulated frames.
20

9. The assembly of claim 1, wherein the pre-encapsulated frame comprises one of a panel of pre-encapsulated frames.

10. The assembly of claim 1, wherein the plurality of traces comprises a
25 plurality of traces configured for connection to a first semiconductor device having bond pads in a one-sided layout and at least another semiconductor device.

11. The assembly of claim 1, wherein the plurality of traces comprises a
plurality of traces configured for connection to a first semiconductor device having the
30 bond pads thereof in a 1.5-sided layout and at least another semiconductor device.

12. The assembly of claim 1, wherein the plurality of traces comprises a plurality of traces configured for connection to a first semiconductor device having the bond pads thereof in a one-sided layout along the long side of the first semiconductor device and at least another semiconductor device.

5

13. The assembly of claim 1, wherein the plurality of traces comprises a plurality of traces configured for connection to a first semiconductor device having the bond pads thereof in a two-sided layout and at least another semiconductor device.

10

14. The assembly of claim 1, wherein the plurality of traces comprises a plurality of traces configured for connection to a first semiconductor device having the bond pads thereof located essentially in the center of the semiconductor device and at least another semiconductor device.

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15. The assembly of claim 1, wherein the plurality of traces comprises a plurality of traces configured for connection to a first semiconductor device having the bond pads thereof located essentially in a single row in the center of the semiconductor device and at least another semiconductor device.

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16. The assembly of claim 1, wherein the plurality of traces comprises a plurality of traces configured for connection to a first semiconductor device having the bond pads thereof located essentially in multiple rows essentially in the center of the semiconductor device and at least another semiconductor device.

25

17. The assembly of claim 1, further comprising:
encapsulation material located in the cavity of the structure.

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18. The assembly of claim 1, wherein the one end of the second portion of a trace of the plurality of traces includes one of a groove therein and a roughened surface thereon.

19. The assembly of claim 1, wherein the second portion of a trace of the plurality of traces comprises a plurality of portions, each portion having one end of the second portion being exposed for connection thereto.